

# P-Channel 30-V (D-S) MOSFET

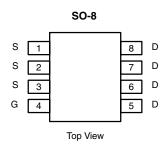
PRODUCT SUMMARY			
V <sub>DS</sub> (V)	$r_{DS(on)}(\Omega)$	I <sub>D</sub> (A)	
-30	0.02 @ V <sub>GS</sub> = -10 V	-8.0	
	0.035 @ V <sub>GS</sub> = -4.5 V	-6.0	

#### **FEATURES**

 Lead (Pb)-Free Version is RoHS Compliant

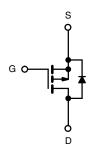


ROHS



Ordering Information: Si4435DY-T1-REV A

Si4435DY-T1-A-E3 (Lead (Pb)-Free)



P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS ( $T_A = 25^{\circ}$ UNLESS OTHERWISE NOTED)						
Parameter	Symbol	Limit	Unit			
Drain-Source Voltage		V <sub>DS</sub>	-30	V		
Gate-Source Voltage		V <sub>GS</sub>	±20	v		
0 11	T <sub>A</sub> = 25°C		-8.0			
Continuous Drain Current (T <sub>J</sub> = 150°C) <sup>a</sup>	T <sub>A</sub> = 70°C	I <sub>D</sub>	-6.4			
Pulsed Drain Current		I <sub>DM</sub>	-50	A		
Continuous Source Current (Diode Conduction) <sup>a</sup>		I <sub>S</sub>	-2.1			
Maximum Power Dissipation <sup>a</sup>	T <sub>A</sub> = 25°C	В	2.5	w		
iviaximum rowei Dissipation~	T <sub>A</sub> = 70°C	P <sub>D</sub>	1.6	VV		
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	-55 to 150	°C		

THERMAL RESISTANCE RATINGS					
Parameter	Symbol	Limit	Unit		
Maximum Junction-to-Ambienta	R <sub>thJA</sub>	50	°C/W		

#### Notes

a. Surface Mounted on FR4 Board,  $t \le 10$  sec.

For SPICE model information via the Worldwide Web: http://www.vishay.com/www/product/spice.htm



SPECIFICATIONS (T <sub>J</sub> = 25°C UNLESS OTHERWISE NOTED)							
Parameter	Symbol	Test Condition	Min	Typ <sup>a</sup>	Max	Unit	
Static	<u>.</u>		•	•	•	•	
Gate Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}, I_D = -250 \mu A$	-1.0	-2.0	-3.0	V	
Gate-Body Leakage	I <sub>GSS</sub>	$V_{DS}$ = 0 V, $V_{GS}$ = $\pm$ 20 V			± 100	nA	
Zono Ooto Valtana Dunin Ourmant		$V_{DS} = -30 \text{ V}, V_{GS} = 0 \text{ V}$		-1			
Zero Gate Voltage Drain Current	l <sub>DSS</sub> —	$V_{DS} = -30 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 70^{\circ}\text{C}$			<b>-</b> 5	μΑ	
0 0 1 D 1 D 1 D		$V_{DS} \le -5 \text{ V}, V_{GS} = -10 \text{ V}$	-40				
On-State Drain Current <sup>b</sup>	I <sub>D(on)</sub>	$V_{DS} \le -5 \text{ V}, V_{GS} = -4.5 \text{ V}$	-10			Α	
D. 1.0		$V_{GS} = -10 \text{ V}, I_D = -8.0 \text{ A}$		0.015	0.02		
Drain-Source On-State Resistance <sup>b</sup>	r <sub>DS(on)</sub>	$V_{GS} = -4.5 \text{ V}, I_D = -5.0 \text{ A}$		0.022	0.035	Ω	
Forward Transconductance <sup>b</sup>	9fs	$V_{DS} = -15 \text{ V}, I_D = -8.0 \text{ A}$		20		S	
Diode Forward Voltage <sup>b</sup>	V <sub>SD</sub>	$I_S = -2.1 \text{ A}, V_{GS} = 0 \text{ V}$		-0.75	-1.2	V	
Dynamic <sup>a</sup>				•	•	•	
Total Gate Charge	$Q_g$			47	60	nC	
Gate-Source Charge	Q <sub>gs</sub>	$V_{DS} = -15 \text{ V}, \ V_{GS} = -10 \text{ V}, \ I_D = -4.6 \text{ A}$		9.5			
Gate-Drain Charge	Q <sub>gd</sub>			8			
Gate Resistance	R <sub>G</sub>			2.75	4.1	Ω	
Turn-On Delay Time	t <sub>d(on)</sub>			16	30	ns	
Rise Time	t <sub>r</sub>	$V_{DD} = -15 \text{ V}, R_1 = 15 \Omega$		17	30		
Turn-Off Delay Time	t <sub>d(off)</sub>	$I_D \cong -1 \text{ A}, V_{GEN} = -10 \text{ V}, R_G = 6 \Omega$		75	120		
Fall Time	t <sub>f</sub>			31	80		
Source-Drain Reverse Recovery Time	t <sub>rr</sub>	$I_F = -2.1 \text{ A}, \text{ di/dt} = 100 \text{ A/}\mu\text{s}$		40	80		

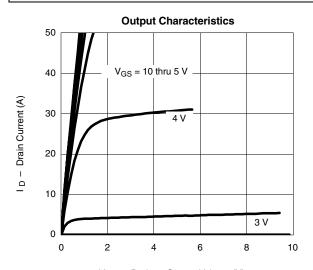
#### Notes

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

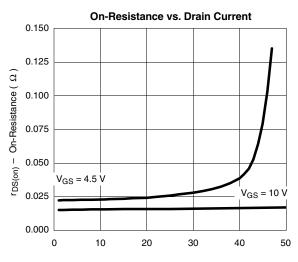
Guaranteed by design, not subject to production testing. Values shown are for Product Revision A. Pulse test; pulse width  $\leq 300~\mu s$ , duty cycle  $\leq 2\%$ .



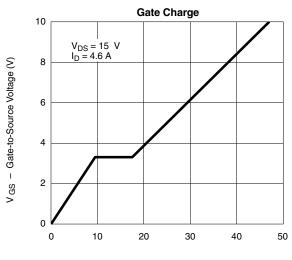
### TYPICAL CHARACTERISTICS, PRODUCT REVISION A (25°C UNLESS NOTED)



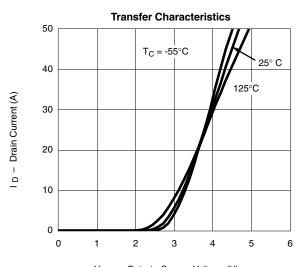
 $V_{DS}\,-\,$  Drain-to-Source Voltage (V)



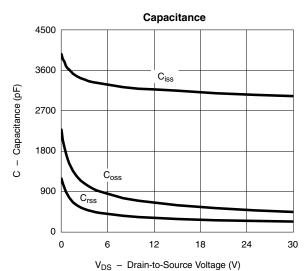
I<sub>D</sub> - Drain Current (A)

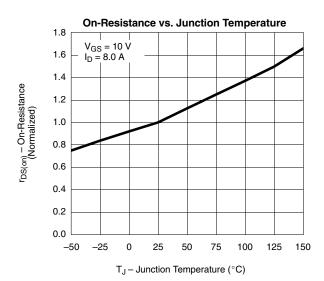


Q<sub>q</sub> - Total Gate Charge (nC)



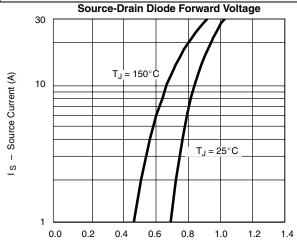
V<sub>GS</sub> - Gate-to-Source Voltage (V)

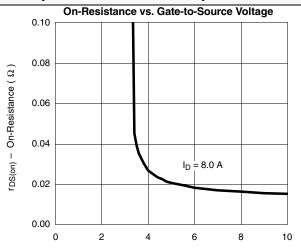


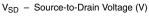


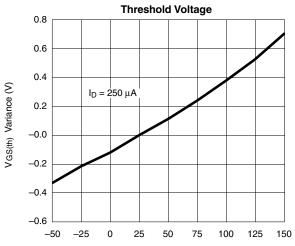


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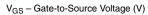


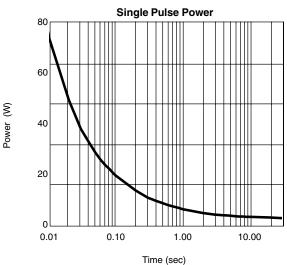




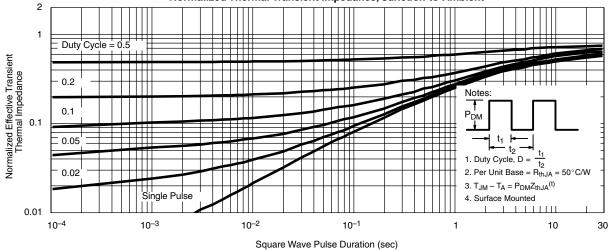


T<sub>J</sub> - Temperature (°C)









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